

SEMICONDUCTOR®

### November 2013

# FQD19N10L N-Channel QFET<sup>®</sup> MOSFET

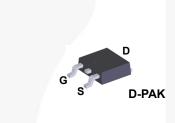
100 V, 15.6 A, 100 mΩ

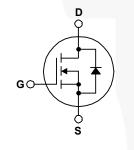
# Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

## Features

- 15.6 A, 100 V,  $R_{DS(on)}$  = 100 m $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V
- Low Gate Charge (Typ. 14 nC)
- Low Crss (Typ. 35 pF)
- 100% Avalanche Tested





## Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

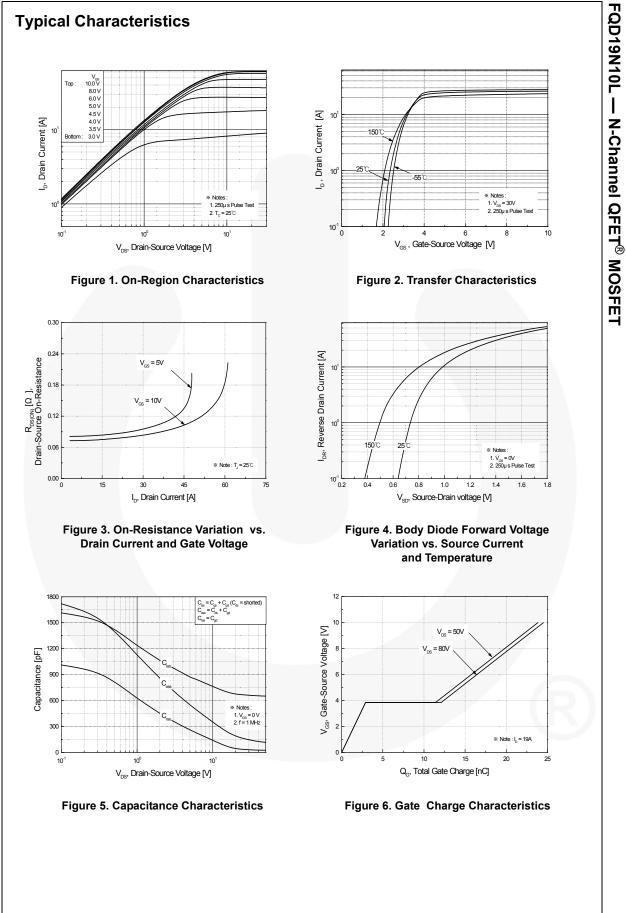
Symbol	Parameter			FQD19N10LTM	Unit	
V <sub>DSS</sub>	Drain-Source V	oltage		100	V	
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°	C)	15.6	A	
		- Continuous (T <sub>C</sub> = 100°C)		9.8	А	
I <sub>DM</sub>	Drain Current	Drain Current - Pulsed		62.4	A	
V <sub>GSS</sub>	Gate-Source Vo	oltage		± 20	V	
E <sub>AS</sub>	Single Pulsed A	valanche Energy	(Note 2)	220	mJ	
I <sub>AR</sub>	Avalanche Curr	ent	(Note 1)	15.6	A	
E <sub>AR</sub>	Repetitive Avala	anche Energy	(Note 1)	5.0	mJ	
dv/dt	Peak Diode Red	covery dv/dt	(Note 3)	6.0	V/ns	
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25°C) *			2.5	W	
	Power Dissipation ( $T_C = 25^{\circ}C$ )			50	W	
		- Derate Above 25°C		0.4	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

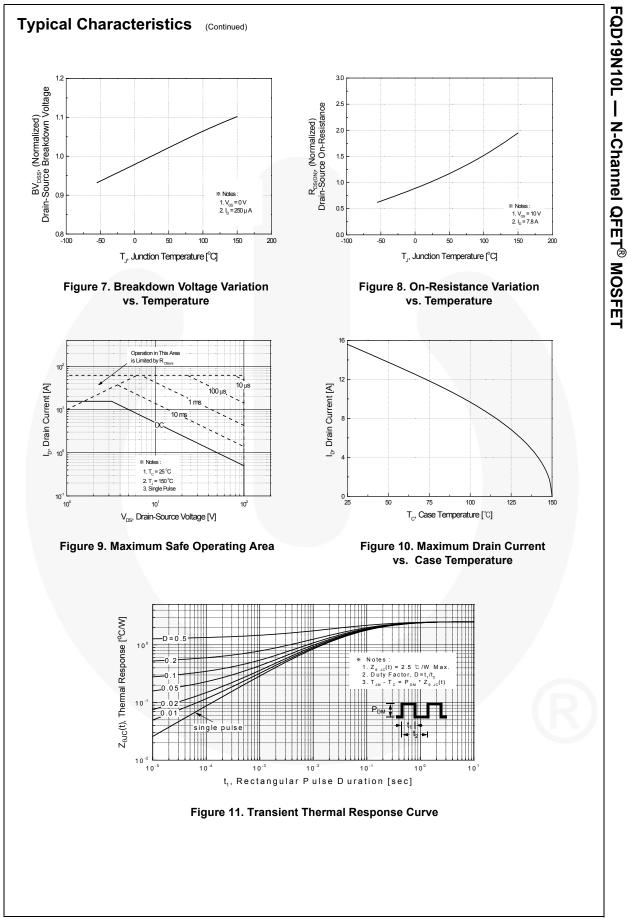
# **Thermal Characteristics**

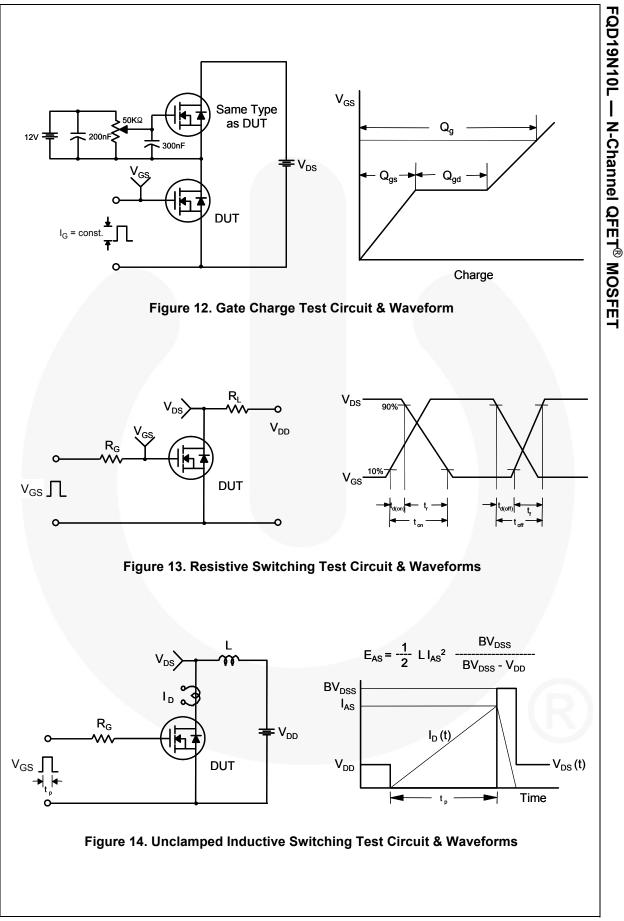
Symbol	Parameter	FQD19N10LTM	Unit
$R_{\thetaJC}$	Thermal Resistance, Junction to Case, Max.	2.5	
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	50	

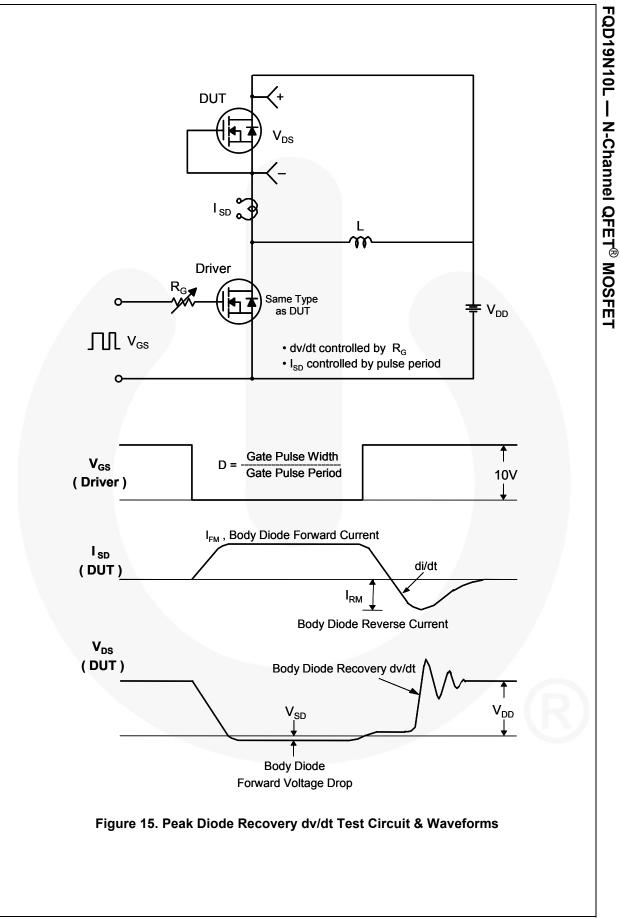
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rain-Source reakdown \ oefficient	<b>s</b> e Breakdown Volt	-		Test Conditions			T		
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rain-Source reakdown \ oefficient	e Breakdown Volt	-							
reakdown \ oefficient		-	V <sub>GS</sub> =	0 V, I <sub>D</sub> = 250 μA		100			V
		Breakdown Voltage Temperature Coefficient		$I_D$ = 250 µA, Referenced to 25°C			0.09		V/°C
ero Gate Vo	Zero Gate Voltage Drain Current		V <sub>DS</sub> =	100 V, V <sub>GS</sub> = 0 V				1	μA
			V <sub>DS</sub> =	80 V, T <sub>C</sub> = 125°C				10	μA
Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse		Forward	$V_{GS} = 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$					100	nA
		$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$					-100	nA	
cteristic	s								
			V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = 250 μA		1.0		2.0	V
Static Drain-Source On-Resistance			V <sub>GS</sub> =	10 V, I <sub>D</sub> = 7.8 A			0.074	0.10	Ω
			V <sub>GS</sub> = 5 V, I <sub>D</sub> = 7.8 A				0.082	0.11	52
Forward Transconductance		$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 7.8 \text{ A}$				14	S	S	
Characte	ristics								
				05.1/.)/ 0.1/			670	870	pF
									pF
		f = 1.0 MHz						pF	
									μ.
Charac	teristics								
urn-On Dela	ay Time		Vpp =	50 V Ip = 19 A			14	38	ns
urn-On Rise	e Time			-			410	830	ns
urn-Off Dela	ay Time		- ··G				20	50	ns
urn-Off Fall	Time				(Note 4)		20		
					(11010 4)		140	290	ns
otal Gate C			V <sub>DS</sub> =	80 V, I <sub>D</sub> = 19 A,	(Note 4)			290 18	ns nC
	harge		V <sub>DS</sub> = V <sub>GS</sub> =	-	(11010 4)		140		
otal Gate C	harge Charge			-	(Note 4)		140 14		nC
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otal Gate C ate-Source ate-Drain C arce Dioc aximum C aximum Pu rain-Source everse Rec	harge : Charge Charge <b>de Characteri</b> ontinuous Drain-S ulsed Drain-Sourc	Source Dic ce Diode F	$V_{GS} =$ hd Ma bde Forvard $V_{GS} =$ $V_{GS} =$	5 V ximum Rating vard Current Current	(Note 4)		140 14 2.9 9.2  	18  15.6 62.4	nC nC nC A A
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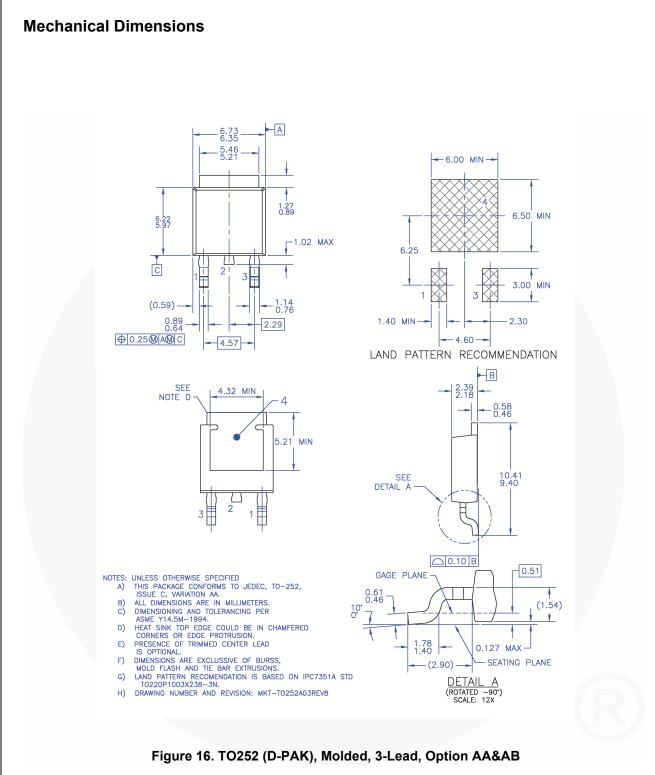
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